

Amendments to the Specification:

Please amend the specification as follows:

Please replace paragraph number [0001] under the title “Cross Reference to Related Applications” with the following rewritten paragraph:

[0001] The present application is related to U.S. Application No. 09/819,342 (Atty. Dkt. No. 39153/403 (F0942)) by Shields et al., entitled “Process for Forming Sub-Lithographic Photoresist Features by Modification of the Photoresist Surface;” U.S. Application No. 09/819,692 (Atty. Dkt. No. 39153/404 (F0943)) by Okoroanyanwu et al., entitled “Process for Preventing Deformation of Patterned Photoresist Features by Electron Beam Stabilization;” U.S. Application No. 09/819,344 (Atty. Dkt. No. 39153/406 (F1061)) by Okoroanyanwu et al., entitled “Process for Reducing the Critical Dimensions of Integrated Circuit Device Features;” U.S. Application No. 09/819,343 (Atty. Dkt. No. 39153/298 (F0785)) by Gabriel et al., entitled “Selective Photoresist Hardening to Facilitate Lateral Trimming;” and U.S. Application No. 09/819,552 (Atty. Dkt. No. 39153/310 (F0797)) by Gabriel et al., entitled “Process for Improving the Etch Stability of Ultra-Thin Photoresist,” all filed on an even date herewith and assigned to the Assignee of the present application.